Toshiyuki Isshiki

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Heteroepitaxial growth of (111) 3C–SiC on well-lattice-matched (110) Si substrates by chemical vapor deposition. Applied Physics Letters, 2004, 84, 3082-3084.	3.3	72
2	Structure and growth mechanism of tetrapod-like ZnO particles. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1997, 76, 889-904.	0.6	55
3	A metastable phase in thermal decomposition of Ca-deficient hydroxyapatite. Journal of Materials Science: Materials in Medicine, 2003, 14, 617-622.	3.6	37
4	Catalytic mechanism of a Fe–Co bimetallic system for efficient growth of single-walled carbon nanotubes on Siâ^•SiO2 substrates. Journal of Applied Physics, 2006, 100, 094303.	2.5	20
5	Application of UV-Raman Spectroscopy for Characterization of the Physical Crystal Structure Following Flash Anneal of an Ultrashallow Implanted Layer. Journal of the Electrochemical Society, 2006, 153, G697.	2.9	16
6	Transmission electron microscopic studies on an initial stage in the conversion process from α-tricalcium phosphate to hydroxyapatite. Journal of Materials Research, 2003, 18, 2633-2638.	2.6	14
7	Ferromagnetism and structural distortions induced in atomized Fe-AI (35–42 at.% AI) powder particles by cold milling. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1999, 79, 2013-2023.	0.6	13
8	Suppression Mechanism of Double Positioning Growth in 3C-SiC(111) Crystal by Using an Off-Axis Si(110) Substrate. Materials Science Forum, 2005, 483-485, 181-184.	0.3	13
9	Fine structure of tooth enamel in the yellowing human teeth: SEM and HRTEM studies. Microscopy Research and Technique, 2016, 79, 14-22.	2.2	12
10	Suppression of the Twin Formation in CVD Growth of (111) 3C-SiC on (110) Si Substrate. Materials Science Forum, 2005, 483-485, 193-196.	0.3	11
11	A preparation method of sections of fine particles and cross-sectional transmission electron microscopy of Ni powder. Journal of Electron Microscopy, 1997, 46, 293-301.	0.9	10
12	Band structure and photoconductivity of blue-green light absorbing AlTiN films. Journal of Materials Chemistry A, 2017, 5, 20824-20832.	10.3	10
13	High-resolution transmission electron microscopy of hexagonal and rhombohedral molybdenum disulfide crystals. Microscopy Research and Technique, 1993, 25, 325-334.	2.2	9
14	Observation of a Latent Scratch on Chemo-Mechanical Polished 4H-SiC Wafer by Mirror Projection Electron Microscopy. Materials Science Forum, 0, 924, 543-546.	0.3	9
15	Three-Dimensional Observation of Internal Defects in a β-Ga2O3 (001) Wafer Using the FIB–SEM Serial Sectioning Method. Journal of Electronic Materials, 2020, 49, 5190-5195.	2.2	9
16	High-resolution transmission electron microscopic observations of grain boundaries and surfaces on Cuî—,Te crystals grown by a solid-solid reaction. Ultramicroscopy, 1987, 23, 355-363.	1.9	8
17	High-resolution transmission electron microscopy of growth and structures of Ag-Te and Cu-Se crystals produced by solid-solid reactions. Journal of Crystal Growth, 1991, 112, 55-70.	1.5	8
18	Synthesis and Raman study of double-walled carbon nanotubes. Diamond and Related Materials, 2007, 16, 1188-1191	3.9	8

Тознічикі Іззнікі

#	Article	IF	CITATIONS
19	Intriguing transmission electron microscopy images observed for perpendicularly oriented cylindrical microdomains of block copolymers. Nanoscale, 2014, 6, 10817-10823.	5.6	8
20	Studies on the growth of pure double-walled carbon nanotube and its phonon spectra. Journal of Applied Physics, 2008, 103, 114305.	2.5	7
21	Preparation of Mesoporous Silica with Well-Defined Hexagonal Array of Pores by Using Octyltrimethylammonium Chloride. Bulletin of the Chemical Society of Japan, 2008, 81, 407-409.	3.2	7
22	Growth and transformation of Cu-Te crystals produced by a solid-solid reaction. Journal of Crystal Growth, 1987, 83, 421-430.	1.5	6
23	Frank Partial Dislocation in 4H-SiC Epitaxial Layer by MSE Method. Materials Science Forum, 2012, 725, 31-34.	0.3	6
24	Non Destructive Inspection of Dislocations in SiC Wafer by Mirror Projection Electron Microscopy. Materials Science Forum, 0, 778-780, 402-406.	0.3	6
25	Contrast of adsorbed or removed atoms in surface profile images by high- and ultra-high-resolution electron microscopy. Ultramicroscopy, 1992, 41, 201-209.	1.9	5
26	Influence of Substrate Roughness on the Formation of Defects in 3C-SiC Grown on Si(110) Substrate by Hetero-Epitaxial CVD Method. Materials Science Forum, 2005, 483-485, 185-188.	0.3	5
27	Transmission electron microscopic observation of a metastable phase on the thermal decomposition process of Ca-deficient hydroxyapatite. Journal of Materials Science, 2006, 41, 525-530.	3.7	5
28	Effective catalyst on SiO2 in ethanol CVD for growth of single-walled carbon nanotubes. Diamond and Related Materials, 2008, 17, 1467-1470.	3.9	5
29	Simultaneous Observation of Single-Walled Carbon Nanotubes and Catalyst Particles on SiO2Substrate by Transmission Electron Microscopy. Japanese Journal of Applied Physics, 2008, 47, 730-734.	1.5	5
30	Structural and electronic properties of Co-doped ZnO nanocrystals synthesized by co-precipitation method. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 213-216.	0.8	5
31	Dislocation Conversion in 4H-SiC Crystals Grown by Metastable Solvent Epitaxy. ECS Journal of Solid State Science and Technology, 2013, 2, N3092-N3097.	1.8	5
32	Study on Formation of Dislocation Contrast in 4H-SiC Wafer in Mirror Projection Electron Microscopy Image. Materials Science Forum, 0, 821-823, 307-310.	0.3	5
33	AFM Observation of Etch-Pit Shapes on β-Ga ₂ 0 ₃ (001) Surface Formed by Molten Alkali Etching. Materials Science Forum, 0, 1004, 512-518.	0.3	5
34	Consolidation Mechanism of Calcium Silicate on Exposure to Carbon Dioxide. Zairyo/Journal of the Society of Materials Science, Japan, 2003, 52, 571-575.	0.2	5
35	Surface profile images of Te crystals by high-resolution transmission electron microscopy. Ultramicroscopy, 1989, 30, 329-336.	1.9	4
36	Habit, structure and surface formation of Te particles deposited in a high-resolution transmission electron microscope. Journal of Crystal Growth, 1992, 125, 7-16.	1.5	4

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#	Article	IF	CITATIONS
37	Multi-slice calculation for InP crystals using different slices. Ultramicroscopy, 1994, 54, 301-309.	1.9	4
38	Dislocation Analysis of 4H-SiC Using KOH Low Temperature Etching. Materials Science Forum, 0, 778-780, 358-361.	0.3	4
39	Relations between Surface Morphology and Dislocations of SiC Crystal. Materials Science Forum, 0, 821-823, 311-314.	0.3	4
40	Basal Plane Dislocation Analysis of 4H-SiC Using Multi Directional STEM Observation. Materials Science Forum, 0, 821-823, 303-306.	0.3	4
41	Characterization of the surface morphology and grain growth near the surface of a block copolymer thin film with cylindrical microdomains oriented perpendicular to the surface. Polymer Journal, 2017, 49, 655-663.	2.7	4
42	Observation of Basal Plane Dislocation in 4H-SiC Wafer by Mirror Projection Electron Microscopy and Low-Energy SEM. Materials Science Forum, 0, 897, 197-200.	0.3	4
43	Au-nanoparticle-embedded cross-linked gelatin films synthesized on aqueous solution in contact with dielectric barrier discharge. Japanese Journal of Applied Physics, 2018, 57, 0102BE.	1.5	4
44	Crystal structure analysis of stacking faults through scanning transmission electron microscopy of β-Ga ₂ O ₃ (001) layer grown via halide vapor phase epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 032701.	2.1	4
45	Broadband Optical Amplification of Waveguide Cutâ€Off Mode in Polymer Waveguide Doped with Graphene Quantum Dots. Advanced Optical Materials, 2022, 10, .	7.3	4
46	High-Resolution Transmission Electron Microscopy of Interfaces between thin Nickel Layers on Si(001) After Nickel Silicide Formation under Various Annealing Conditions. , 2006, , .		3
47	Highly Aligned Growth of Carbon Nanotubes by RF-Plasma-Assisted DC Plasma Chemical Vapor Deposition at High Pressure. Japanese Journal of Applied Physics, 2006, 45, 8308-8310.	1.5	3
48	Observation of Pair Structures of Threading Dislocation and Surface Defect in 4H-SiC Wafer by Mirror Projection Electron Microscopy. Materials Science Forum, 0, 858, 371-375.	0.3	3
49	Electronic structure of AlFeN films exhibiting crystallographic orientation change from c- to a-axis with Fe concentrations and annealing effect. Scientific Reports, 2020, 10, 1819.	3.3	3
50	Reducing structural change in aluminum coated polyethylene naphthalate foils during MeV proton irradiation. Vacuum, 2013, 89, 153-156.	3.5	2
51	Surface morphology and dislocation characteristics near the surface of 4H-SiC wafer using multi-directional scanning transmission electron microscopy. Journal of Electron Microscopy, 2017, 66, 337-347.	0.9	2
52	Chemical Trend in Band Structure of 3d-Transition-Metal-Doped AlN Films. Materials Science Forum, 0, 924, 322-325.	0.3	2
53	Defects Characterization of GaN Substrate with Hot Implant Process. Materials Science Forum, 0, 1004, 497-504.	0.3	2
54	Structures of grain boundaries in long-chain te crystals observed by high-resolution transmission electron microscopy. Microscopy Research and Technique, 1992, 23, 207-218.	2.2	1

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55	Non-Contact, Non-Destructive Characterization of Crystal Quality in Ultra-Shallow ion Implanted Silicon Wafers Before and after Annealing. , 2006, , .		1
56	Multi-Wavelength Raman and HRTEM Study of Ni/Si Interface after NiSi Formation at Low Temperatures using Various Heating Methods. ECS Transactions, 2008, 13, 405-412.	0.5	1
57	TEM Observation of Defect Structure of Low-Energy Ion Implanted SiC. Materials Science Forum, 0, 778-780, 350-353.	0.3	1
58	STEM and HRTEM studies of accumulated deposits on human tooth surface. Microscopy Research and Technique, 2017, 80, 511-524.	2.2	1
59	Three Dimensional Dislocation Analysis of Threading Mixed Dislocation Using Multi Directional Scanning Transmission Electron Microscopy. Materials Science Forum, 2017, 897, 173-176.	0.3	1
60	Observation of Dislocation Conversion in 4H-SiC Epitaxial Wafer by Mirror Projection Electron Microscopy. Materials Science Forum, 2019, 963, 251-254.	0.3	1
61	Microstructure of Stacking Fault Complex/Carrot Defects at Interface Between 4H-SiC Epitaxial Layers and Substrates. Journal of Electronic Materials, 2020, 49, 5213-5218.	2.2	1
62	Review and Detail Classification of Stacking Faults in 4H-SiC Epitaxial Layer by Mirror Projection Electron Microscopy. Materials Science Forum, 0, 1004, 314-320.	0.3	1
63	Synthesis of Phosphate Glass Coating Film by Pulsed Laser Deposition. Zairyo/Journal of the Society of Materials Science, Japan, 2007, 56, 777-780.	0.2	1
64	Chemical element of the outermost layer of AgBr single crystal. Applied Surface Science, 1992, 55, 287-291.	6.1	0
65	Transmission Electron Microscopic Study on Thermal Decomposition Process of Calcium-Deficient Hydroxyapatite. Key Engineering Materials, 2006, 317-318, 785-788.	0.4	0
66	Deep-UV Raman Scattering Analysis of Re-Crystallization in Ultra-Shallow Junction Implanted Si under Various Annealing Conditions. , 2007, , .		0
67	Structural Analysis of ZnO Thin Films Grown in Room Temperature on PET Film. Materials Science Forum, 2014, 778-780, 1201-1205.	0.3	0
68	Cross Section and Plan View STEM Analysis on Identical Conversion Point of Basal Plane Dislocation to Threading Edge Dislocation of 4H-SiC. Materials Science Forum, 2016, 858, 397-400.	0.3	0
69	Crystallographic properties of 3d transition metal (Ti, V, and Cr) doped AlN films. , 2016, , .		0
70	Surface Plasmon Resonances in Sn: In2O3 Thin Films with Diffraction Grating. Proceedings (mdpi), 2018, 2, .	0.2	0
71	Crystal Defect Analysis of Latent Scratch Induced during CMP Process on 4H-SiC Wafer Using Electron Microscopy. Materials Science Forum, 2018, 924, 531-534.	0.3	0
72	Structural Characterization of Prismatic Stacking Faults of Two Types of Carrot Defects in 4H-SiC Epi Wafers. Materials Science Forum, 0, 1004, 421-426.	0.3	0

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73	Formation of various-axis-oriented wurtzite nuclei and enlargement of the <i>a</i> -axis-oriented region in AlFeN films deposited on Si(100) substrates. Materials Advances, 2021, 2, 4075-4080.	5.4	0